

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Er r o r s
1	BRS	L25	11	resistor same semiconductor same (conduct\$3 or metal\$3) same ("wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:46			0
2	BRS	L31	11	resistor same semiconductor same (conduct\$3 or metal\$3 or barrier) same ("wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:49			0
3	BRS	L37	0	resistor same semiconductor same (TiW and Al) same ("wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:50			0
4	BRS	L43	1	resistor same semiconductor same (TiW and Al) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:55			0
5	BRS	L49	9	resistor same (TiW and Al) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:15			0
6	BRS	L55	849	resistor same (TiW and Al or electrode) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:16			0
7	BRS	L61	1435	resistor same (TiW and Al or electrode or metal) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:17			0
8	BRS	L67	1166	61 and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:18			0
9	BRS	L73	1567	resistor same (TiW or Al or electrode or metal) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:35			0
10	BRS	L79	1277	73 and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:45			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m en ts	Er ror De fin iti on	Er ror s
11	BRS	L85	11606 3	438/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:18			0
12	BRS	L91	252	85 and 79	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:19			0
13	BRS	L97	62624	resistor same (TiW or Al or electrode or metal) same "wet etching"	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:47			0
14	BRS	L103	1308	(97 and @pd<=19980728) and 85	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:46			0
15	BRS	L109	27	resistor same ((TiW or Al or electrode or metal) near10 "wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 12:30			0
16	BRS	L139	8	(TiW and Al) same "wet etching"	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 12:39			0
17	BRS	L145	20	TiW and Al) same( "wet etching" or contacting	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 12:40			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Er r o r s
1	BRS	L25	11	resistor same semiconductor same (conduct\$3 or metal\$3) same ("wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:46			0
2	BRS	L31	11	resistor same semiconductor same (conduct\$3 or metal\$3 or barrier) same ("wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:49			0
3	BRS	L37	0	resistor same semiconductor same (TiW and Al) same ("wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:50			0
4	BRS	L43	1	resistor same semiconductor same (TiW and Al) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 10:55			0
5	BRS	L49	9	resistor same (TiW and Al) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:15			0
6	BRS	L55	849	resistor same (TiW and Al or electrode) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:16			0
7	BRS	L61	1435	resistor same (TiW and Al or electrode or metal) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:17			0
8	BRS	L67	1166	61 and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:18			0
9	BRS	L73	1567	resistor same (TiW or Al or electrode or metal) same etching	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:35			0
10	BRS	L79	1277	73 and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 14:54			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Er r o r s
11	BRS	L85	11606 3	438/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:18			0
12	BRS	L91	252	85 and 79	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:19			0
13	BRS	L97	62624	resistor same (TiW or Al or electrode or metal) same "wet etching"	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:47			0
14	BRS	L103	1308	(97 and @pd<=19980728) and 85	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 11:46			0
15	BRS	L109	27	resistor same ((TiW or Al or electrode or metal) near10 "wet etching")	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 12:30			0
16	BRS	L139	8	(TiW and Al) same "wet etching"	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 12:39			0
17	BRS	L145	20	TiW and Al) same( "wet etching" or contacting	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 14:35			0
18	BRS	L151	0	(TiW and Al) same ("wet etching" or contacting) same laminat\$3	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 14:38			0
19	BRS	L157	9	(TiW and Al) same laminating	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 14:46			0
20	BRS	L163	1446	(wet etching and laminating) same ((barrier or TiW or " titanium tungsten") and (metal or Al or aluminum))	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:06			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co m m e n t s	Er r o r D e f i n i t i o n	Er r o r s
21	BRS	L169	215	(163 and 85) and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:06			0
22	BRS	L175	1397	(wet etching near10 laminating) same ((barrier or TiW or " titanium tungsten") and (metal or Al or aluminum))	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:08			0
23	BRS	L181	208	(175 and 85) and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:11			0
24	BRS	L187	0	("wet etching" near10 laminating) same ((barrier or TiW or " titanium tungsten") and (metal or Al or aluminum))	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:09			0
25	BRS	L193	0	("wet etching" near5 laminating) same ((barrier or TiW or " titanium tungsten") and (metal or Al or aluminum))	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:09			0
26	BRS	L199	0	("wet etching" and laminating) same ((barrier or TiW or " titanium tungsten") and (metal or Al or aluminum))	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 17:38			0
27	BRS	L205	545	(etch\$3 and laminat\$3) same ((barrier or TiW or " titanium tungsten") and (metal or Al or aluminum))	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:37			0
28	BRS	L211	116	(205 and 85) and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:39			0
29	BRS	L217	207	(etch\$3 and laminat\$3) same (barrier or metal or conduct\$3) same resistor	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:39			0
30	BRS	L223	1	("207" and 85) and @pd<=19980728	USPAT; EPO; JPO; DERWENT; IBM TDB	2001/12/10 15:39			0